

L Number	Hits	Search Text	DB	Time stamp
9	6976	361/\$.ccls. and card	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 18:57
10	157534	438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 18:55
11	3546	438/365.ccls. or 438/378.ccls. or 438/455.ccls. or 438/597.ccls. or 438/598.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 18:58
14	2546	361/\$.ccls. and card near10 (memory or smart or ic or "integrated circuit")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 19:16
15	2742	(438/365.ccls. or 438/378.ccls. or 438/455.ccls. or 438/597.ccls. or 438/598.ccls.) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 18:59
16	549	361/\$.ccls. and card near10 (memory or smart or ic or "integrated circuit") same (stack\$4 or small)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 19:16
-	2372	235/492.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:51
-	238	(hsieh.in. or wu.in. or chen.in.) and stacked near3 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:52
-	59	(hsieh.in. or wu.in. or chen.in.) and stacked near3 memory and upper and lower	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:52
-	0	(hsieh.in. or wu.in. or chen.in.) and stacked near3 memory and upper and lower and glue	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:53
-	5473	stack\$5 near4 card	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:55
-	225	stack\$5 near4 card and hole and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:55
-	112	stack\$5 near4 card and hole and substrate and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:56
-	1964	("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and hole and substrate and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:58
-	1213	("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and hole and substrate and chip and (upper or top) same (lower or bottom)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 18:59
-	525	("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and hole and substrate and chip and (upper or top) same (lower or bottom) and stack\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:01

-	60	stack\$5 same ("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and hole and substrate and chip and (upper or top) same (lower or bottom)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:02
-	89	stack\$5 same ("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and (vias or hole) and substrate and chip and (upper or top) same (lower or bottom)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:22
-	37	stack\$5 same ("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and (vias or hole) and substrate and chip and (upper or top) same (lower or bottom) same card	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:13
-	10	stack\$5 same ("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and (vias or hole) and substrate and chip and (upper or top) same (lower or bottom) and sink	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:33
-	17	stack\$5 same ("memory card" or smart-card or "smart card" or ((ic or "integrated circuit") near1 card)) and (vias or hole) and substrate and chip and (upper or top) same (lower or bottom) and (copper or aluminum or sink) same heat	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/15 19:34